| -( | 5 | • •     |            |    |
|----|---|---------|------------|----|
|    |   | SEMIKRO | SKT 1000/1 | ZT |
|    |   |         |            |    |

**Capsule Thyristor** 

| Line | Thyristor |
|------|-----------|
|------|-----------|

#### SKT 1000

#### Features

- Hermetic metal case with ceramic insulator
- Capsule package for double sided cooling
- International standard case
- Off-state and reverse voltages up to 2800 V
- Amplifying gate

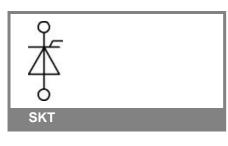
#### **Typical Applications**

- DC motor control (e. g. for machine tools)
- Controlled rectifiers (e. g. for battery charging)
- AC controllers (e. g. for temperature control)
- Recommended snubber network

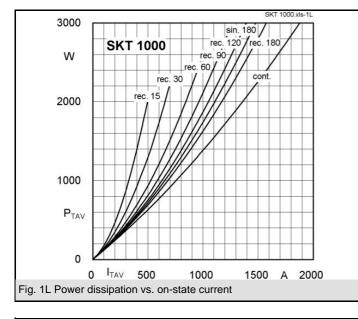
e. g. for V<sub>VRMS</sub> 
$$\leq$$
 400 V:  
R = 33 Ω/32 W, C = 1 µF

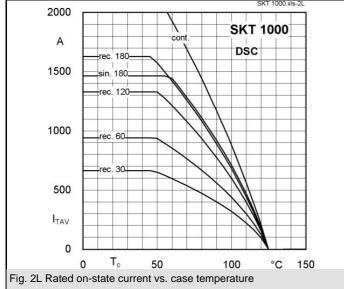
| V <sub>RSM</sub> | V <sub>RRM</sub> , V <sub>DRM</sub> | I <sub>TRMS</sub> = 2300 A (maximum value for continuous operation) |  |  |
|------------------|-------------------------------------|---|--|--|
| V                | V                                   | I <sub>TAV</sub> = 1000 A (sin. 180; DSC; T <sub>c</sub> = 85 °C)   |  |  |
| 1300             | 1200                                | SKT 1000/12E  |  |  |
| 1700             | 1600                                | SKT 1000/16E  |  |  |
| 2300             | 2200                                | SKT 1000/22EL2  |  |  |
| 2700             | 2600                                | SKT 1000/26EL2  |  |  |
| 2900             | 2800                                | SKT 1000/28EL2  |  |  |

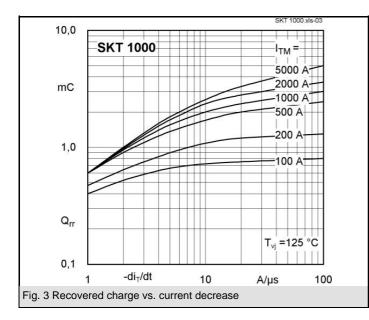
| Symbol                            | Conditions  | Values         | Units |
|-----------------------------------|---|----------------|-------|
| I <sub>TAV</sub>                  | sin. 180; T <sub>c</sub> = 100 (85) °C                                      | 710 (1000 )    | А     |
| I <sub>D</sub>                    | 2 x P8/180; T <sub>a</sub> = 45 °C; B2 / B6                                 | 360 / 500      | А     |
|                                   | 2 x P8/180F; T <sub>a</sub> = 35 °C; B2 / B6                                | 1250 /1750     | А     |
| I <sub>RMS</sub>                  | 2 x P8/180; T <sub>a</sub> = 45 °C; W1C                                     | 400            | А     |
| I <sub>TSM</sub>                  | T <sub>vi</sub> = 25 °C; 10 ms  | 19000          | Α     |
|                                   | T <sub>vi</sub> = 125 °C; 10 ms   | 16500          | А     |
| i²t                               | T <sub>vj</sub> = 25 °C; 8,3 10 ms  | 1800000        | A²s   |
|                                   | T <sub>vj</sub> = 125 °C; 8,3 10 ms   | 1360000        | A²s   |
| V <sub>T</sub>                    | T <sub>vi</sub> = 25 °C; I <sub>T</sub> = 3600 A                            | max. 2         | V     |
| V <sub>T(TO)</sub>                | T <sub>vi</sub> = 125 °C  | max. 1,14      | V     |
| r <sub>T</sub>                    | T <sub>vj</sub> = 125 °C  | max. 0,243     | mΩ    |
| I <sub>DD</sub> ; I <sub>RD</sub> | $T_{vj}$ = 125 °C; $V_{RD}$ = $V_{RRM}$ ; $V_{DD}$ = $V_{DRM}$              | max. 100       | mA    |
| t <sub>gd</sub>                   | T <sub>vj</sub> = 25 °C; I <sub>G</sub> = 1 A; di <sub>G</sub> /dt = 1 A/μs | 1              | μs    |
| t <sub>gr</sub>                   | $V_{\rm D} = 0.67 * V_{\rm DRM}$  | 2              | μs    |
| (di/dt) <sub>cr</sub>             | T <sub>vi</sub> = 125 °C  | max. 125       | A/µs  |
| (dv/dt) <sub>cr</sub>             | T <sub>vi</sub> = 125 °C  | max. 1000      | V/µs  |
| t <sub>q</sub>                    | T <sub>vi</sub> = 125 °C  | 100 250        | μs    |
| I <sub>H</sub>                    | T <sub>vj</sub> = 25 °C; typ. / max.  | 250 / 500      | mA    |
| I <sub>L</sub>                    | T <sub>vj</sub> = 25 °C; R <sub>G</sub> = 33 Ω; typ. / max.                 | 500 / 2000     | mA    |
| V <sub>GT</sub>                   | T <sub>vi</sub> = 25 °C; d.c.   | min. 5         | V     |
| I <sub>GT</sub>                   | T <sub>vj</sub> = 25 °C; d.c.   | min. 250       | mA    |
| V <sub>GD</sub>                   | $T_{vj} = 125 \text{ °C; d.c.}$   | max. 0,25      | V     |
| I <sub>GD</sub>                   | T <sub>vj</sub> = 125 °C; d.c.  | max. 10        | mA    |
| R <sub>th(j-c)</sub>              | cont.; DSC  | 0,021          | K/W   |
| R <sub>th(j-c)</sub>              | sin. 180; DSC / SSC   | 0,0225 / 0,054 | K/W   |
| R <sub>th(j-c)</sub>              | rec. 120; DSC / SSC   | 0,027 / 0,06   | K/W   |
| R <sub>th(c-s)</sub>              | DSC / SSC   | 0,005 / 0,01   | K/W   |
| T <sub>vj</sub>                   |   | - 40 + 125     | °C    |
| T <sub>stg</sub>                  |   | - 40 + 130     | °C    |
| V <sub>isol</sub>                 |   | -              | V~    |
| F                                 | mounting force  | 22 25          | kN    |
| а                                 |   |                | m/s²  |
| m                                 | approx.   | 480            | g     |
| Case                              |   | B 14           |       |
|                                   |   |                |       |
|                                   |   |                |       |

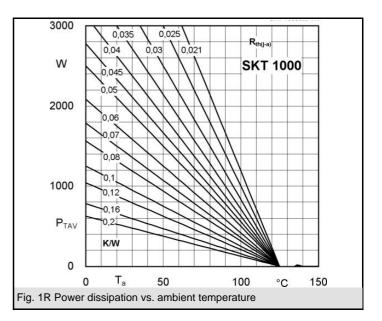


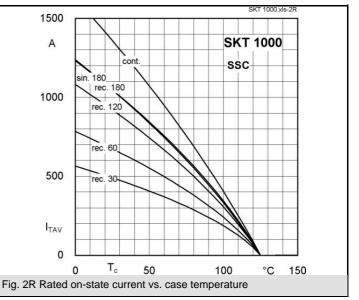
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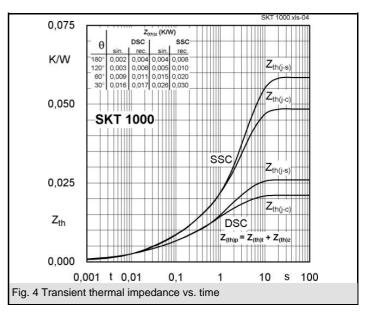




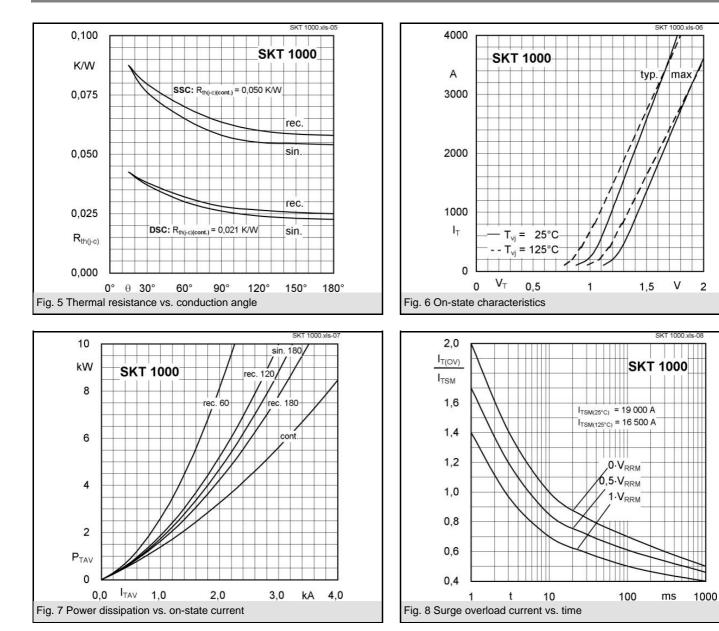


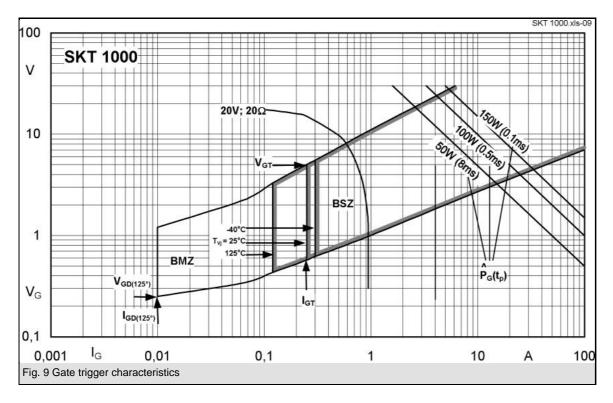


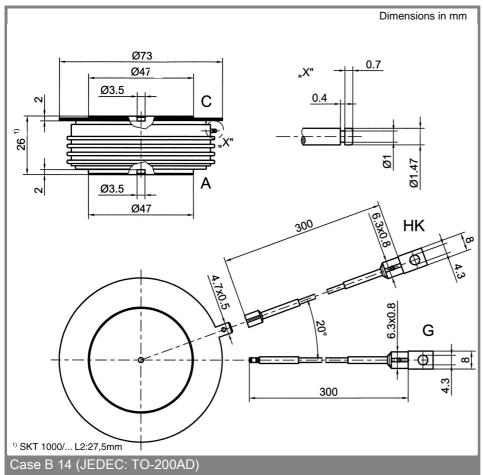




#### 25-04-2005 NOS







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